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RENESAS TECHNICAL UPDATE

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Product Category	MPU/MCU		Document No.	TN-RX*-A042A/E	Rev.	1.00
Title	Errata to RX210 Group User's Manual regarding ROM Characteristics		Information Category	Technical Notification		
Applicable Product	RX210 Group	Lot No. All	Reference Document	RX210 Group User's Manual: Hardware Rev.1.10 (R01UH0037EJ0110)		

This document describes corrections to Table 41.52 in 41.11 "ROM (Flash Memory for Code Storage) Characteristics" in RX210 Group User's Manual: Hardware Rev.1.10.

[Corrections]

Corrected descriptions of the reprogramming/erasure cycle and data hold time in Table 41.52 "ROM (Flash Memory for Code Storage) Characteristics (1)" as follows:

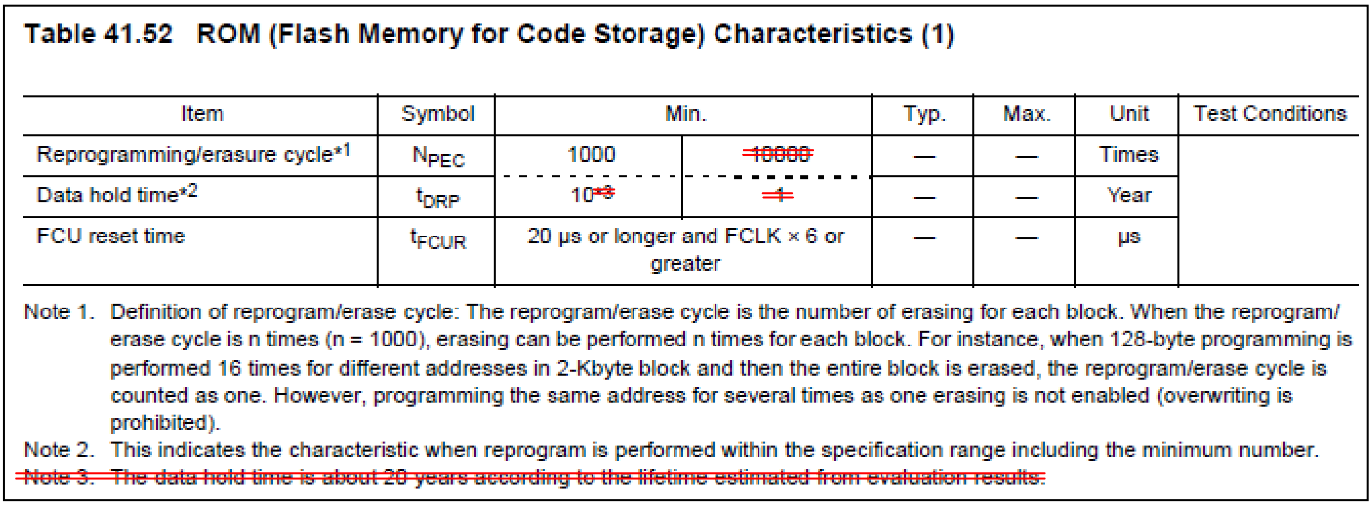

Table 41.52 ROM (Flash Memory for Code Storage) Characteristics (1)

Item	Symbol	Min.		Typ.	Max.	Unit	Test Conditions
Reprogramming/erasure cycle*1	N_{PEC}	1000	~~10000~~	—	—	Times	
Data hold time*2	t_{DRP}	10~~*3~~	~~1~~	—	—	Year	
FCU reset time	t_{FCUR}	20 µs or longer and FCLK × 6 or greater		—	—	µs	

Note 1. Definition of reprogram/erase cycle: The reprogram/erase cycle is the number of erasing for each block. When the reprogram/erase cycle is n times (n = 1000), erasing can be performed n times for each block. For instance, when 128-byte programming is performed 16 times for different addresses in 2-Kbyte block and then the entire block is erased, the reprogram/erase cycle is counted as one. However, programming the same address for several times as one erasing is not enabled (overwriting is prohibited).

Note 2. This indicates the characteristic when reprogram is performed within the specification range including the minimum number.

~~Note 3. The data hold time is about 20 years according to the lifetime estimated from evaluation results.~~